

**Notice of References Cited**

Application/Control No.

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Applicant(s)/Patent Under  
Reexamination  
AMMON ET AL.

Examiner

Johannes P Mondt

Art Unit

2826

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,191,009 B1	02-2001	Tamatsuka et al	438/471
	B	US-6,299,982 B1	10-2001	Tamatsuka et al	428/446
	C	US-5,942,032	08-1999	Kim et al	117/13
	D	US-6,224,668 B1	05-2001	Tamatsuka et al	117/84
	E	US-6,197,109 B1	03-2001	Iida et al	117/19
*	F	US-4,210,486	07-1980	Schmidt et al	156/601
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
*	N	DE-3545383A1	07-1987	Germany	Jacob	H01 L 21/22
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Surma, B. et al, "Effect of Pressure treatment on Electrical Properties of Hydrogen - Doped Silicon", ASDAM'98, 2 <sup>nd</sup> Int. Conf. on Advanced Semiconductor Devices and Microsystems, SWmolenice Castle, Slovakia, 5-7 October 1998.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.